



Title of Change:	Datasheet update for NCV5700/NCD5700/01 series, DESAT charge current.	
Effective date:	4 April 2018	
Contact information:	Contact your local ON Semiconductor Sales Office or <Zarfaq.Jaffery@onsemi.com>	
Type of notification:	This Product Bulletin is for notification purposes only. ON Semiconductor will proceed with implementation of this change upon publication of this Product Bulletin.	
Change category:	<input type="checkbox"/> Wafer Fab Change <input type="checkbox"/> Assembly Change <input checked="" type="checkbox"/> Test Change <input type="checkbox"/> Other _____	
Change Sub-Category(s):	<input type="checkbox"/> Manufacturing Site Change/Addition <input type="checkbox"/> Material Change <input checked="" type="checkbox"/> Datasheet/Product Doc change <input type="checkbox"/> Manufacturing Process Change <input type="checkbox"/> Product specific change <input type="checkbox"/> Shipping/Packaging/Marking <input type="checkbox"/> Other: _____	
Sites Affected:	ON Semiconductor Sites: ON Carmona, Philippines	External Foundry/Subcon Sites: None

Description and Purpose:

Based on additional test data, we are widening the limits for parameter I_{DESAT-CHG} to improve the yield. There is no change to the current product form, fit, or function. The new specification reflects a guard banded limit, enabling ON Semiconductor maintain its high quality standards.

New Datasheet

DESAT PROTECTION

DESAT Threshold Voltage	V _{DESAT-THR}	6.0	6.35	7.0	V
Blanking Charge Current	I _{DESAT-CHG}	0.20	0.24	0.28	mA
Blanking Discharge Current	I _{DESAT-DIS}		30		mA

Current Datasheet

DESAT PROTECTION

DESAT Threshold Voltage	V _{DESAT-THR}	6.0	6.35	7.0	V
Blanking Charge Current	I _{DESAT-CHG}	0.22	0.25	0.28	mA
Blanking Discharge Current	I _{DESAT-DIS}		30		mA

List of Affected Standard Parts:

- NCD5700DR2G
- NCD5701ADR2G
- NCD5701BDR2G
- NCD5701CDR2G
- NCV5700DR2G
- SNCV5700DR2G